

Docket No.: WMP-IFT-679

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Date: October 15, 2003

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applic. No. : 10/662,793
Applicant : Alfred Hesener
Filed : September 15, 2003
Art Unit : to be assigned
Examiner : to be assigned

Docket No. : WMP-IFT-679
Customer No. : 24131

INFORMATION DISCLOSURE STATEMENT

Hon. Commissioner for Patents

Sir:

In accordance with 37 C.F.R. 1.98 copies of the following patents and/or publications are submitted herewith:

United States Patent No. 4,541,041 (Park et al.), dated September 10, 1985;

United States Patent No. 4,855,888 (Henze et al.), dated August 8, 1989;


German Published Non-Prosecuted Patent Application DE 32 41 738 A1
(Raducanu), dated May 17, 1984, and English abstract thereof;

Jens Peer Stengl et al.: "Leistungs-MOS-FET-Praxis" [power MOSFET practice],
Pflaum Verlag, München, 2nd ed., 1992, pp. 173-176;

U. Tietze et al.: "Halbleiter-Schaltungstechnik" [semiconductor circuit technology],
*Springer Verlag, Berlin, 9th ed., pp. 561-576, and pp. 502-515 of the corresponding
English translation.*

If no translation of pertinent portions of any foreign language patents or publications mentioned above is included with the aforementioned copies of those applications, patents and/or publications, it is because no existing translation is readily available to the applicant.

Respectfully submitted,


For Applicant

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Date: October 15, 2003

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FORM PTO-1449 (SUBSTITUTE)

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

Attorney Docket No.:

WMP-IFT-679

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10/662,793

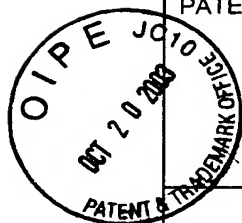
Applicant

Alfred Hesener

Filing Date

September 15, 2003

Group Art Unit

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT
(37 CFR 1.98(b))

U.S. PATENT DOCUMENTS

EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
	A	4,541,041	09/10/85	Park et al.			
	B	4,855,888	08/08/89	Henze et al.			
	C						
	D						
	E						
	F						
	G						
	H						
	I						

FOREIGN PATENT DOCUMENT

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES NO
	J	32 41 738 A1	05/17/84	Germany			X
	K						
	L						
	M						
	N						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

	O	Jens Peer Stengl et al.: "Leistungs-MOS-FET-Praxis" [power MOSFET practice], <i>Pflaum Verlag, München, 2nd ed., 1992, pp. 173-176</i>
	P	U. Tietze et al.: "Halbleiter-Schaltungstechnik" [semiconductor circuit technology], <i>Springer Verlag, Berlin, 9th ed., pp. 561-576, and pp. 502-515 of the corresponding English translation</i>

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.